

TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SD2461

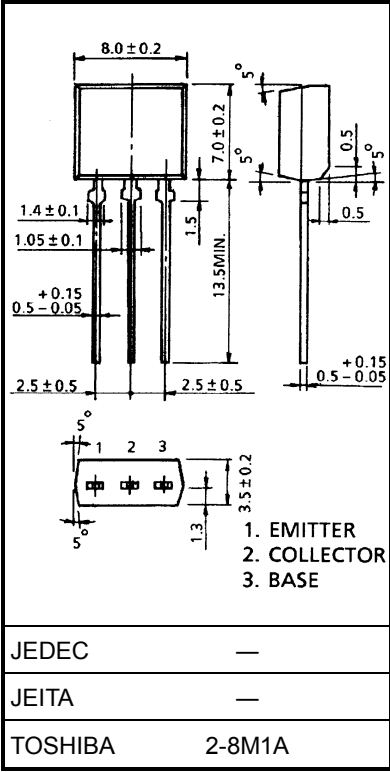
Power Amplifier Applications

- High DC current gain: $h_{FE} (1) = 800$ to 3200 ($V_{CE} = 5\text{ V}$, $I_C = 0.1\text{ A}$)
- Low saturation voltage: $V_{CE} (\text{sat}) = 0.3\text{ V}$ (typ.) ($I_C = 0.5\text{ A}$, $I_B = 5\text{ mA}$)

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	60	V
Collector-emitter voltage		V_{CEO}	60	V
Emitter-base voltage		V_{EBO}	7	V
Collector current	DC	I_C	2	A
	Pulse	I_{CP}	4	
Base current		I_B	0.4	A
Collector power dissipation		P_C	1.3	W
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Unit: mm

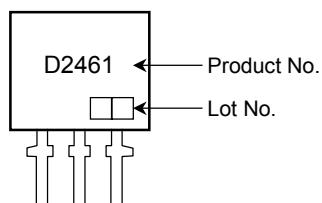


Weight: 0.55 g (typ.)

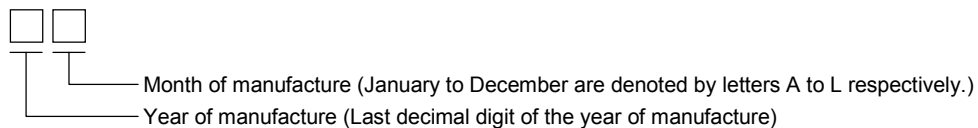
Electrical Characteristics (Ta = 25°C)

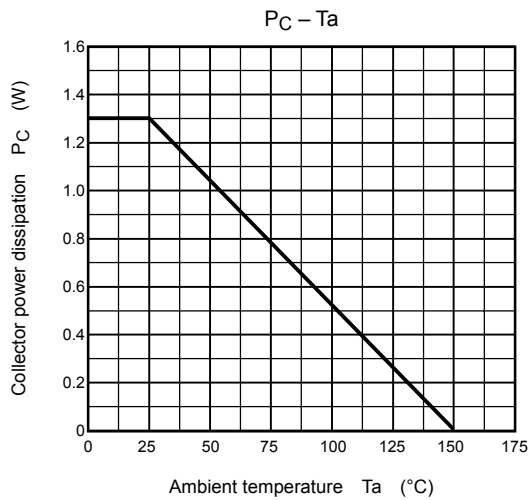
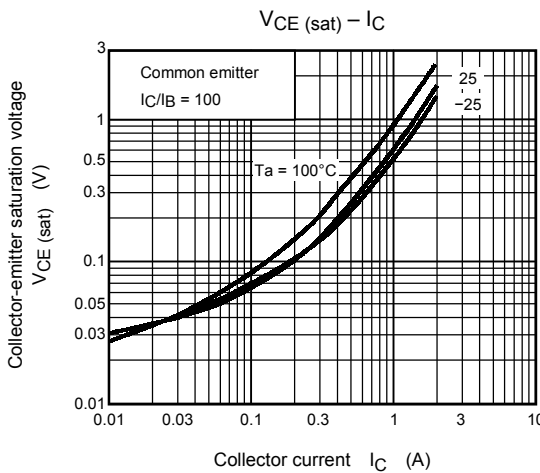
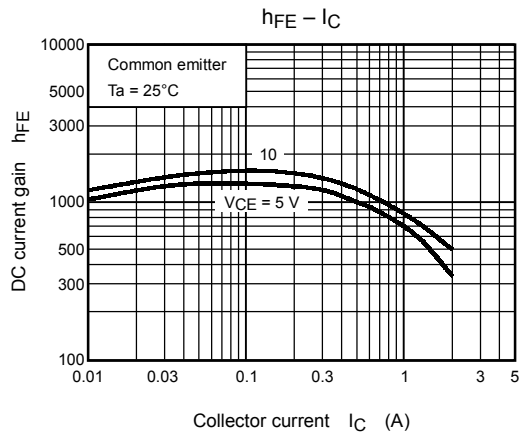
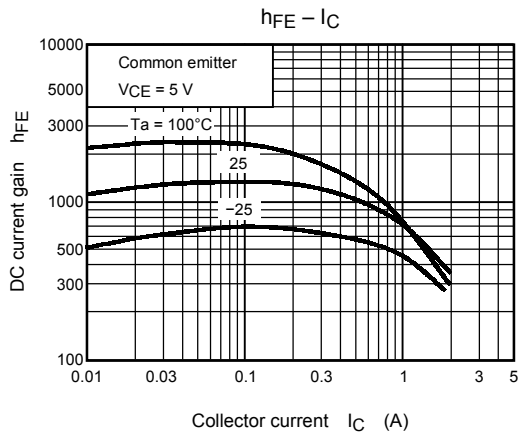
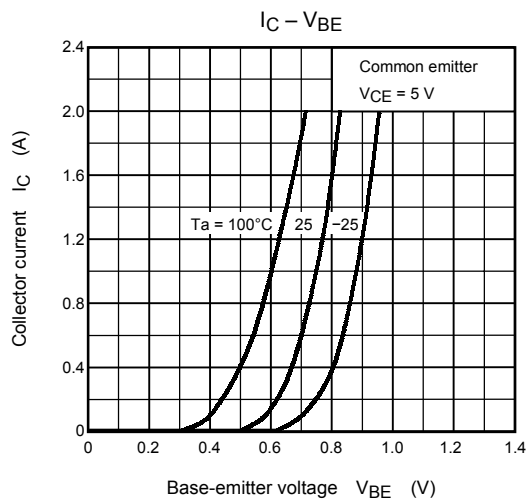
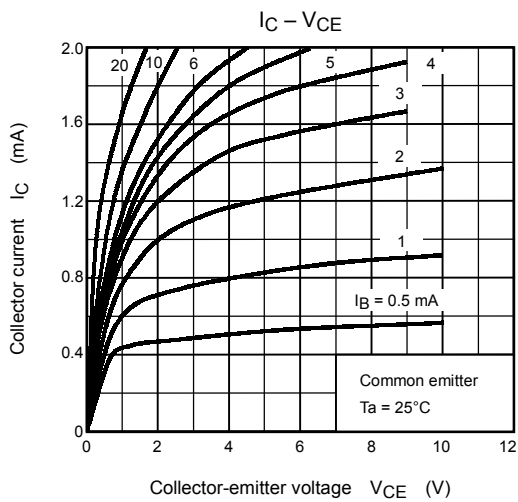
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 60\text{ V}, I_E = 0$	—	—	100	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$	—	—	100	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 50\text{ mA}, I_B = 0$	60	—	—	V
DC current gain	$h_{FE(1)}$	$V_{CE} = 5\text{ V}, I_C = 0.1\text{ A}$	800	—	3200	
	$h_{FE(2)}$	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	350	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 0.5\text{ A}, I_B = 5\text{ mA}$	—	0.3	1.0	V
Base-emitter voltage	V_{BE}	$V_{CE} = 5\text{ V}, I_C = 0.5\text{ A}$	—	0.7	1.0	V
Transition frequency	f_T	$V_{CE} = 5\text{ V}, I_C = 0.5\text{ A}$	—	17	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	30	—	pF

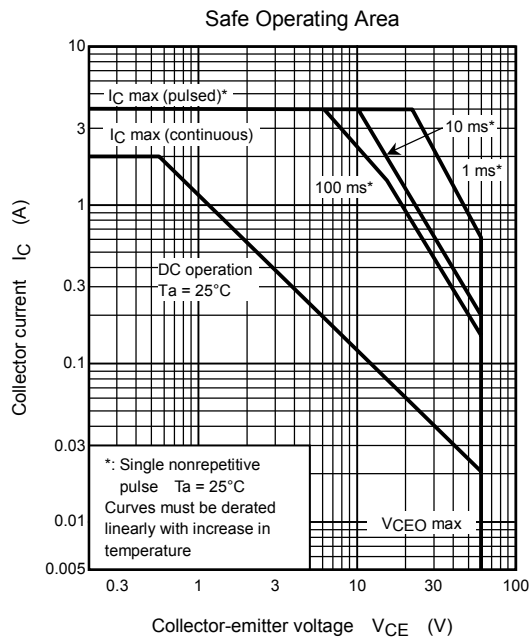
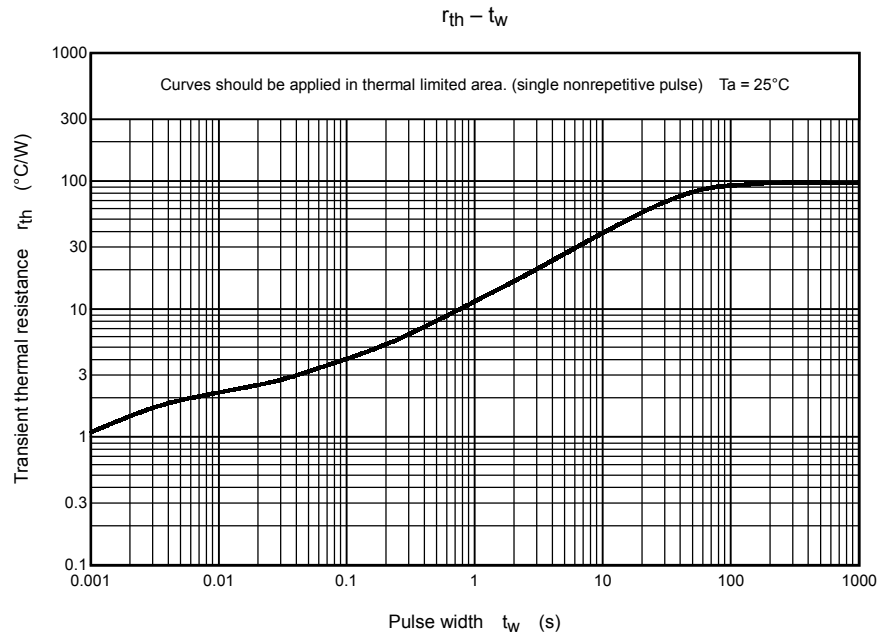
Marking



Explanation of Lot No.







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